



**JST41T-800BW 40**

Peak gate power	$P_{GM}$	40	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.5	kV

( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	50	mA
$V_{GT}$		- -	MAX.	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				200	
$I_H$	$I_T=500mA$		MAX.	100	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	2000	V/ $\mu s$

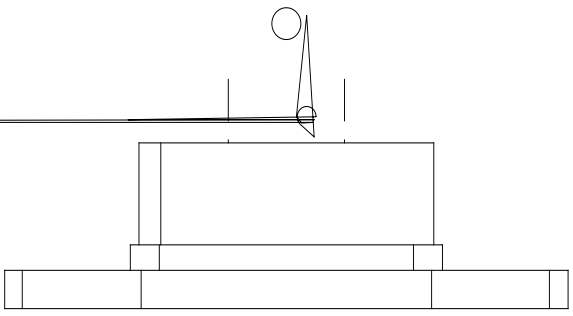
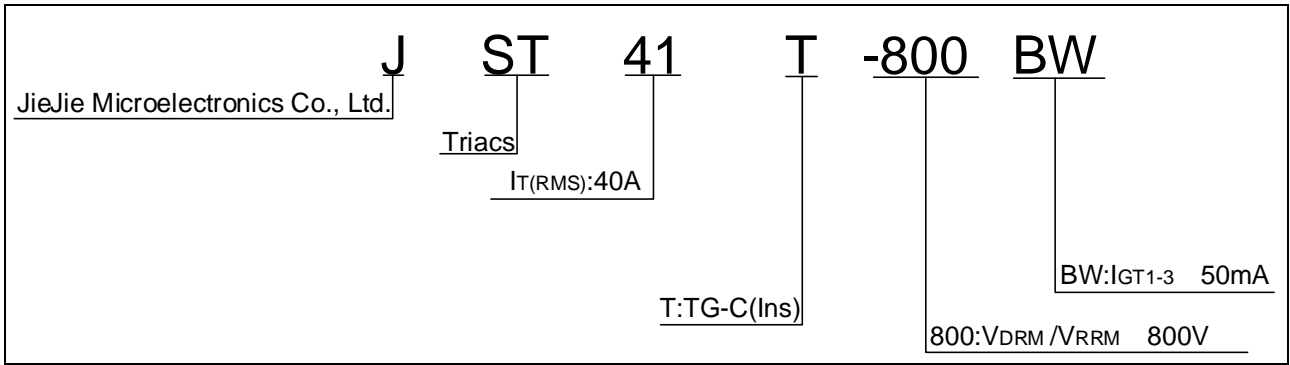
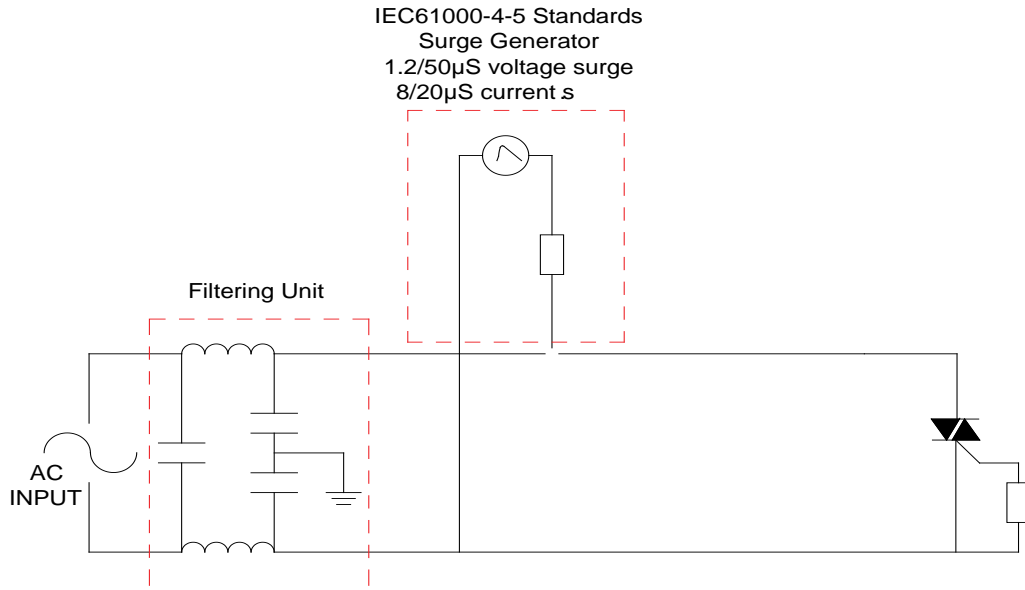




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage $V_{DRM}/V_{RRM}(V)$	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
<b>JST41T-800BW</b>	<b>800</b>	<b>50</b>	<b>TG-C(Ins)</b>	<b>10</b>	<b>Tube</b>

**Document Revision History**

Date	Revision	Changes
Apr.11, 2023	A.1.0	



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